FORM PTO-1449 (modified)
To: U.S. Department of Commerce
(PW FORM PAT-1449)
Patent and Trademark Office

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| Atty. Dkt. No. | M# | Client Ref. |
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| | 284163 | 01F181 |

J1017 U.S. PTO 10/042264 01/11/02

**INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

Applicant: INABA

Appln. No.:

Filing Date: Herewith

Date: January 11, 2002 Page 1 of 1

Examiner: Group Art Unit:

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